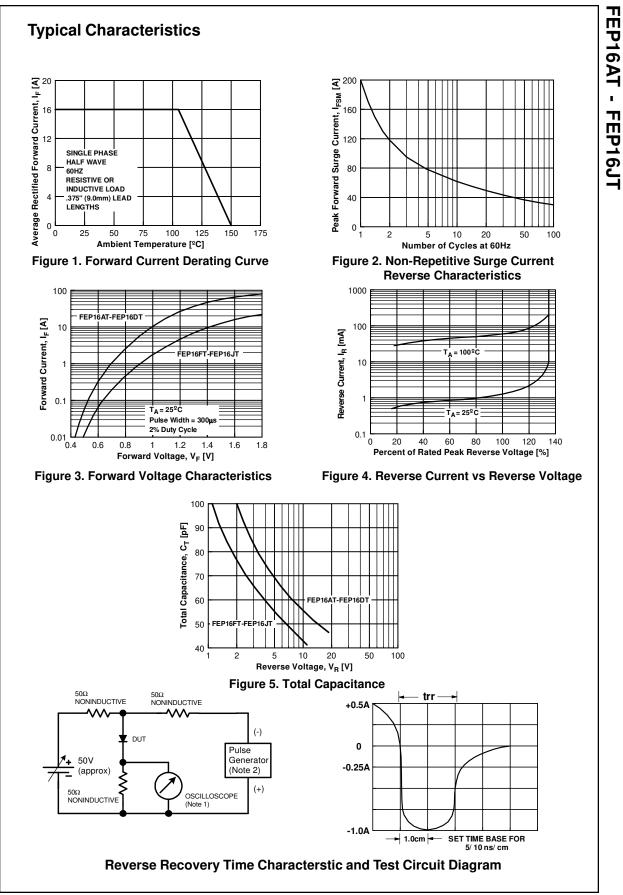
SEMIC	FEP16	AT	- F	EP	16J	IT		PIN 1 O PIN 3 O Positiv	PI	+ D ASE N 2
eatures								PIN 1 O-	₩	
	vard voltage drop. ge current capacity.							PIN 3 O	PI ive CT	ASE N 2
-	rent capability.							Suffix	NI	
High reli		тс)-220A	В				PIN 1 0-		ÁSE
-	Forward Current Rating at 16A (8)	A per	Diode)					Double	er Pl	N 2
-		-						Suffix	"D"	
Fast F	lectifiers (Glass Pas	Siva	ated)						
Absolu	te Maximum Ratings*	T _ 25°C	unloss of	therwise r	otod					
	to maximum natingo	A = 25 C	uness of		loteu					
Symbol	Parameter	16AT	16BT	16CT	Va 16DT	alue 16FT	16GT	16HT	16JT	Units
Symbol	Parameter Maximum Repetitive Reverse Voltage	16AT 50	16BT 100	16CT 150			16GT 400	16HT 500	16JT 600	Units V
-	Maximum Repetitive Reverse Voltage Average Rectified Forward Current,				16DT	16FT				
V _{RRM}	Maximum Repetitive Reverse Voltage Average Rectified Forward Current, .375 " lead length @ T _A = 100°C Non-repetitive Peak Forward Surge Current				16DT 200	16FT 300				V
V _{RRM} I _{F(AV)} I _{FSM}	Maximum Repetitive Reverse Voltage Average Rectified Forward Current, .375 " lead length @ $T_A = 100^{\circ}C$ Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave				16DT 200	16FT 300 16 200	400			V A A
V _{RRM} I _{F(AV)}	Maximum Repetitive Reverse Voltage Average Rectified Forward Current, .375 " lead length @ T _A = 100°C Non-repetitive Peak Forward Surge Current				16DT 200 2 -55 t	16FT 300 16	400			V
V _{RRM} I _{F(AV)} I _{FSM} T _{stg} T _J	Maximum Repetitive Reverse VoltageAverage Rectified Forward Current, .375 " lead length @ $T_A = 100^{\circ}C$ Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-WaveStorage Temperature Range Operating Junction Temperature	50	100	150	16DT 200 -55 t -55 t	16FT 300 16 200 30 +150 30 +150 30 +150	400			V A A °C
V _{RRM} I _{F(AV)} I _{FSM} T _{stg} T _J	Maximum Repetitive Reverse VoltageAverage Rectified Forward Current, .375 " lead length @ $T_A = 100^{\circ}C$ Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-WaveStorage Temperature Range	50	100	150	16DT 200 -55 t -55 t	16FT 300 16 200 30 +150 30 +150 30 +150	400			V A A °C
$\frac{V_{\text{RRM}}}{I_{\text{F(AV)}}}$ $\frac{I_{\text{FSM}}}{T_{\text{J}}}$ These ratings a	Maximum Repetitive Reverse VoltageAverage Rectified Forward Current, .375 " lead length @ $T_A = 100^{\circ}C$ Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-WaveStorage Temperature Range Operating Junction Temperature	50	100	150	16DT 200 -55 t -55 t	16FT 300 16 200 30 +150 30 +150 30 +150	400			V A A °C
V_{RRM} $I_{F(AV)}$ I_{FSM} T_{J} These ratings a	Maximum Repetitive Reverse Voltage Average Rectified Forward Current, .375 " lead length @ $T_A = 100^{\circ}C$ Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave Storage Temperature Range Operating Junction Temperature are limiting values above which the serviceability of an	50	100	150	16DT 200 -55 t -55 t	16FT 300 16 200 30 +150 30 +150 30 +150	400			V A A °C
V_{RRM} $I_{F(AV)}$ I_{FSM} T_{J} These ratings a	Maximum Repetitive Reverse Voltage Average Rectified Forward Current, 375 " lead length @ $T_A = 100^{\circ}C$ Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave Storage Temperature Range Operating Junction Temperature rre limiting values above which the serviceability of an	50	100	150	16DT 200 -55 t -55 t	16FT 300 16 200 200 30 +150 30 +150 3d.	400			V A A °C °C
$\frac{V_{RRM}}{I_{F(AV)}}$ $\frac{I_{FSM}}{T_{J}}$ These ratings a Therma Symbol	Maximum Repetitive Reverse Voltage Average Rectified Forward Current, .375 " lead length @ $T_A = 100^{\circ}C$ Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave Storage Temperature Range Operating Junction Temperature are limiting values above which the serviceability of an I Characteristics Parameter	50 y semicor	100	150	16DT 200 -55 t -55 t	16FT 300 16 200 0 +150 0 +150 o +150 od.	400			V A A ○C ○C

Symbol	Parameter	Device								
		16AT	16BT	16CT	16DT	16FT	16GT	16HT	16JT	1
V _F	Forward Voltage @ 8.0A	0.95			1.3		1.5		V	
t _{rr}	Reverse Recovery Time $I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{BR} = 0.25 \text{ A}$	35				50				ns
I _R	Reverse Current @ rated V_R $T_A = 25^{\circ}C$ $T_A = 100^{\circ}C$	10 500						μΑ μΑ		
C _T	Total Capacitance $V_B = 4.0. f = 1.0 MHz$	85 60						0	pF	



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